

# N-channel TrenchMOS logic level FET Rev. 4 — 20 July 2011

Product data sheet

#### 1. **Product profile**

#### **1.1 General description**

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

#### 1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems

#### General purpose power switching

Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	75	V
I <sub>D</sub>	drain current	$V_{GS} = 5 V; T_{mb} = 25 °C;$ see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u> _	-	75	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	300	W
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C	-	4.7	5.5	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 11; see Figure 12	-	5.2	6.1	mΩ



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Table 1.	Quick reference data	acontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} &I_D = 75 \text{ A};  \text{V}_{\text{sup}} \leq 75 \text{ V}; \\ &R_{\text{GS}} = 50  \Omega;  \text{V}_{\text{GS}} = 5 \text{ V}; \\ &T_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	-	852	mJ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 60 V; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	37	-	nC

[1] Continuous current is limited by package.

#### **Pinning information** 2.

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Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make a connection to pin 2.

#### **Ordering information** 3.

#### Table 3. **Ordering information**

Type number	Package				
	Name	Description	Version		
BUK9606-75B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

### 4. Limiting values

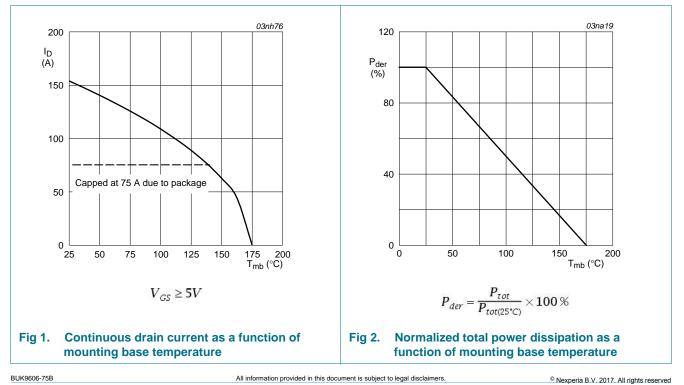
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>i</sub> ≥ 25 °C; T <sub>i</sub> ≤ 175 °C	-	75	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	75	V
V <sub>GS</sub>	gate-source voltage		-15	15	V
I <sub>D</sub>	drain current	$T_{mb}$ = 100 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u>	<u>[1]</u> -	75	А
	$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{2};$	[2] _	153	А	
		see Figure 3	<u>[1]</u> -	75	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; see <u>Figure 3</u>	-	612	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	300	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[2] -	153	А
			<u>[1]</u> -	75	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	612	А
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 75 A; V <sub>sup</sub> ≤ 75 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; unclamped	-	852	mJ

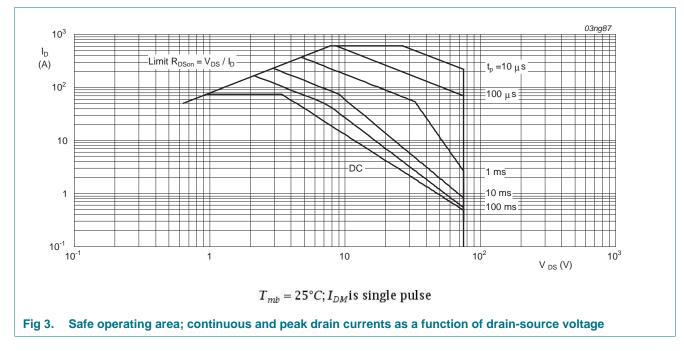
[1] Continuous current is limited by package.

[2] Current is limited by power dissipation chip rating.



## BUK9606-75B

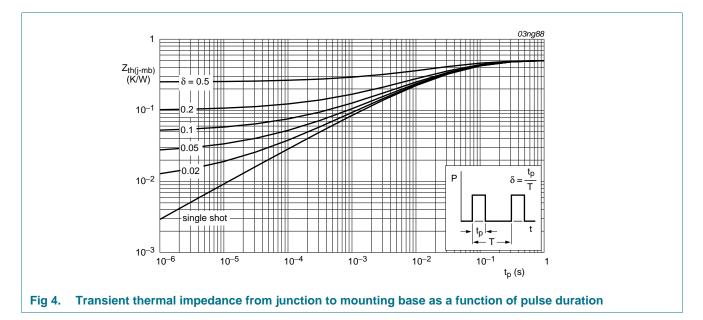
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### 5. Thermal characteristics

#### Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on a printed circuit board; minimum footprint	-	50	-	K/W



### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	75	-	-	V
	breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	70	-	-	V
V <sub>GS(th)</sub> gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	1.1	1.5	2	V	
	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 10</u>	0.5	-	-	V	
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 10</u>	-	-	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 15 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -15 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	-	6.6	mΩ
resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	12.8	mΩ	
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>i</sub> = 25 °C	-	4.7	5.5	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11; see Figure 12	-	5.2	6.1	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 60 \text{ V}; V_{GS} = 5 \text{ V};$	-	95	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	17	-	nC
Q <sub>GD</sub>	gate-drain charge		-	37	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	8770	11693	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	842	1010	pF
C <sub>rss</sub>	reverse transfer capacitance		-	336	460	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	68	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C	-	144	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	273	-	ns
t <sub>f</sub>	fall time		-	116	-	ns
L <sub>D</sub>	internal drain inductance	from drain lead 6 mm from package to centre of die; T <sub>j</sub> = 25 °C	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad; $T_j = 25 \text{ °C}$	-	7.5	-	nH

Symbol

Source-drain diode

## BUK9606-75B

Max

Unit

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Тур

Min

$V_{SD}$	source-drain voltage	$I_S = 40 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25$ see <u>Figure 15</u>	°C;	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$		-	68	-	ns
Qr	recovered charge	$V_{GS}$ = -10 V; $V_{DS}$ = 25 V; $T_j$ =	25 °C	-	176	-	nC
35(		03ng84	8 [			03ng83	
350 I <sub>D</sub> (A) 300		R <sub>DSo</sub> (mΩ)	n				
250		_	7				
200			6				
150 100		3V -	5				
50							
0		2.4 — 8 10 V <sub>DS</sub> (V)	4 0 5		10 VG	15 SS (V)	
	$T_j = 25^{\circ}C; t_p = 300\mu$	is	$T_j =$	= 25°C;I <sub>D</sub> =	= 25A		
	Output characteristics: drair function of drain-source volt		Drain-source of gate-source				Inction
10 <sup>-1</sup>	1 / +/ +/ +/	03ng53 20	0			03ng81	
I <sub>D</sub> (A) 10 <sup>-2</sup>		9fs / (S)					
10 <sup>-3</sup>		15 nax	0				
10~~							
		10	0				
10 <sup>-4</sup>			0				
10 <sup>-4</sup> 10 <sup>-5</sup>							
10 <sup>-4</sup>		5			40 ID	60 (A)	
10 <sup>-4</sup> 10 <sup>-5</sup>		S VGS (V)		25°C;V <sub>DS</sub> =	١ <sub>D</sub>		

#### Table 6. Characteristics ...continued

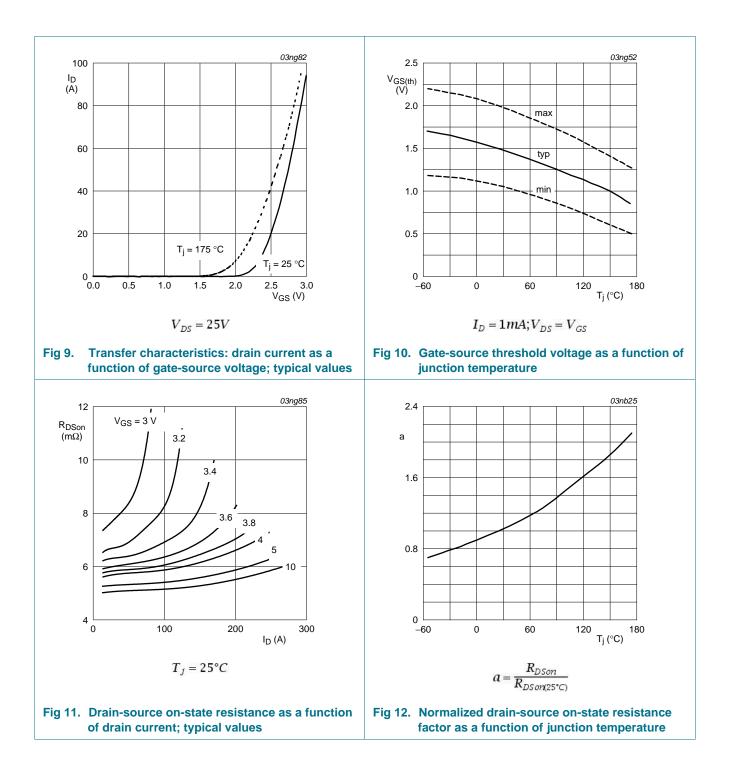
Parameter

Conditions

BUK9606-75B Product data sheet

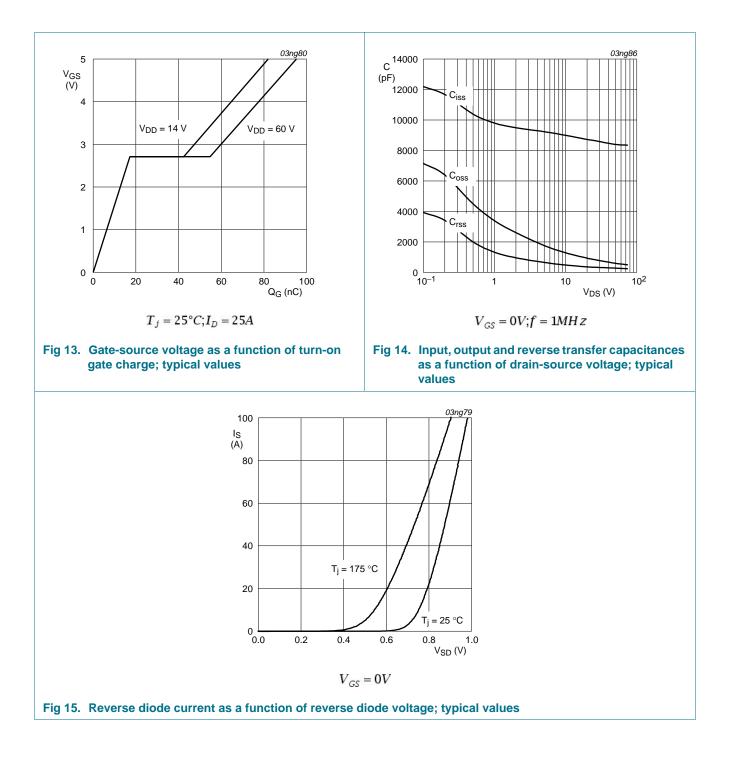
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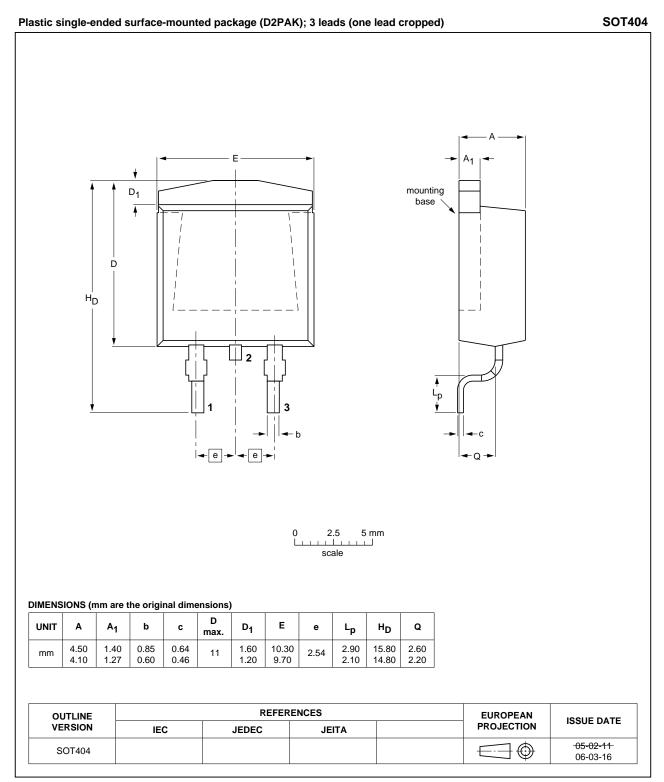
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### 7. Package outline



#### Fig 16. Package outline SOT404 (D2PAK)

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### 8. Revision history

Table 7.	Revision	history
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Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9606-75B v.4	20110720	Product data sheet	-	BUK9606-75B v.3
Modifications:	<ul> <li>Various changes to</li> </ul>	o content.		
BUK9606-75B v.3	20110207	Product data sheet	-	BUK95_9606_75B v.2

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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